

## AMENDMENTS

Please amend the application as follows:

### In the Claims

Please substitute the following clean copy text for the pending claims 1 - 5.

- B1  
Sub E1
1. (amended twice) A transistor circuit for implementing a switch, comprising:
- a first switch node configured to connect to an external circuit;
  - a second switch node configured to connect to the external circuit;
  - a transistor device having a first terminal electrically communicating with the first switch node, a second terminal connected to the second switch node, and a third terminal configured to receive a control signal that controls the electrical connectivity between the first terminal and the second terminal;
  - a third switch node for receiving the control signal; and
  - a circuit connected to the third switch node and the third terminal of the transistor device, the circuit having a sufficiently high impedance to prevent the third switch node from functioning as an alternating current (AC) ground during operation of the switch and thereby reduce the parasitic capacitance between the first terminal and the second terminal of the transistor device.

- B2  
Sub E5
2. (amended once) The transistor circuit of claim 1, wherein the transistor device is a metal-oxide-semiconductor field-effect transistor.

SUB  
C2  
Cmt  
B2

3. (amended once) A transistor circuit for implementing a switch, comprising:  
a first switch node configured to connect to an external circuit;  
a second switch node configured to connect to the external circuit;  
a transistor device having a first terminal connected to the first switch node, a second terminal connected to the second switch node, and a third terminal configured to receive a control signal for controlling the electrical connectivity between the first terminal and the second terminal; and  
a circuit connected to the second terminal of the transistor device, the circuit configured to provide a voltage to the second terminal when the control signal engages the transistor device to reduce parasitic effects at the first terminal when the transistor circuit functions as an open circuit, thereby reducing noise injected to the external circuit at the first switch node.

Sub  
E5

4. (amended once) The transistor circuit of claim 3, wherein the transistor device is a metal-oxide-semiconductor field-effect transistor.

5. (amended once) The transistor circuit of claim 3, wherein the circuit is an inverter circuit.

#### REMARKS

This is a full and timely response to the outstanding Final Office Action mailed April 30, 2002. Reconsideration and allowance of the application and presently pending claims are respectfully requested.